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AMENDMENTS TO THE CLAIMS

1. (Previously Presented) A positive photoresist composition comprising:

(A) an alkali-soluble novolak resin having a weight average molecular weight of 1,000 to 50,000, in which a portion of hydrogen atoms of phenolic hydroxyl groups are substituted with 1.2-naphthoquinonediazidesulfonyl groups; and

(B) a dissolution promoter comprising at least one compound selected from the group consisting of compounds represented by a general formula (b-1) and a general formula (b-11) shown below:

wherein, R^1 to R^9 each represent, independently, a hydrogen atom, an alkyl group, a halogen atom, or a hydroxyl group, although at least one of R^1 to R^9 represents a hydroxyl group; and R^{10} to R^{15} each represent, independently, a hydrogen atom, an alkyl group, an alkenyl group, a cycloalkyl group or an aryl group;

$$(H^{42})_s$$
 $(H^{41})_r$ $(H^{43})_t$ $(H^{43})_t$

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wherein, R^{41} to R^{43} each represent, independently, a lower alkyl group, a cycloalkyl group or a lower alkoxy group; p and q each represent an integer from 1 to 3; and r, s and t each represent either 0, or an integer from 1 to 3.

- (Original) A positive photoresist composition according to claim 1, wherein said component (A) is a fractionated resin in which fractionation treatment has been used to reduce a lower molecular weight fraction to no more than 80% by weight of a value prior to said fractionation.
- (Original) A positive photoresist composition according to claim 1, further comprising a photosensitizer (C),
- (Original) A positive photoresist composition according to claim 1, which comprises both (b-1) and (b-11) as dissolution promoters.
- 5. (Previously presented) A method of forming a resist pattern comprising the steps of applying a positive photoresist composition according to any one of claim 1 through claim 4 to a substrate, conducting a prebake, performing selective exposure, and then performing alkali developing to form said resist pattern.
- (Previously presented) The positive photoresist composition according to claim
 wherein said component (A) has a weight average molecular weight of 2,000 to 20,000.
- (Previously presented) The positive photoresist composition according to claim
 wherein the quantity of said component (C) within said positive photoresist composition,

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relative to the combined quantity of said component (A) and said component (B), is 30% by weight or less.

- 8. (Previously presented) The positive photoresist composition according to claim 1, wherein the proportion of the hydrogen atoms of the phenolic hydroxyl groups substituted with 1,2-naphthoquinonediazidesulfonyl groups within said component (A) is from 2 to 10 mol%.
- 9. (New) The positive photoresist composition according to claim 1, formed into a resist pattern on a substrate, wherein said resist pattern is at least 3 μ m in thickness.